

# MJE340G;ON;TO126;tranzystor; NPN;500mA;300V;21W;Pbf



### Dane techniczne:

Nazwa: MJE340G Typ tranzystora: bipolarny Kierunek przewodnictwa: NPN Prąd kolektora: 500mA Napięcie kolektor-emiter: 300V Moc: 21W Montaż: przewlekany(THT) Obudowa: TO126 Producent: ON

www.podzespoly-elektroniczne.pl

## **Plastic Medium-Power NPN Silicon Transistor**

This device is useful for high-voltage general purpose applications.

### Features

- Suitable for Transformerless, Line-Operated Equipment
- Thermopad Construction Provides High Power Dissipation Rating for High Reliability
- These Devices are Pb-Free and are RoHS Compliant\*
- Complementary to MJE350

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	300	Vdc
Emitter–Base Voltage	V <sub>EB</sub>	3.0	Vdc
Collector Current – Continuous	Ι <sub>C</sub>	500	mAdc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	20 0.16	W mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$\theta_{JC}$	6.25	°C/W

### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	V <sub>CEO(sus)</sub>	300	-	Vdc
Collector Cutoff Current ( $V_{CB} = 300 \text{ Vdc}, I_E = 0$ )	I <sub>CBO</sub>	-	100	μAdc
Emitter Cutoff Current ( $V_{EB} = 3.0 \text{ Vdc}, I_C = 0$ )	I <sub>EBO</sub>	_	100	μAdc
ON CHARACTERISTICS				
DC Current Gain	h <sub>FE</sub>			_

 $(I_C = 50 \text{ mAdc}, V_{CE} = 10 \text{ Vdc})$ 240 30 Product parametric performance is indicated in the Electrical Characteristics for

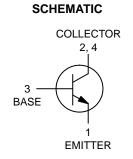
the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



### **ON Semiconductor®**

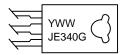
http://onsemi.com

### 0.5 AMPERE POWER TRANSISTOR NPN SILICON **300 VOLTS, 20 WATTS**





### MARKING DIAGRAM



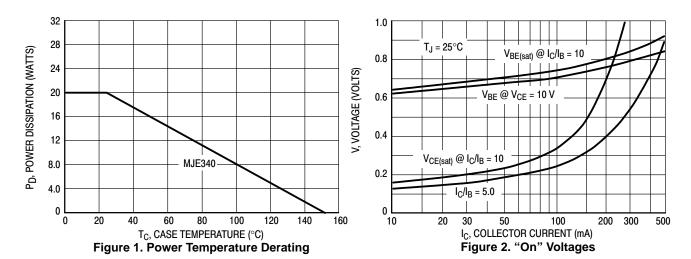
= Year Y WW = Work Week JE340 = Device Code G

= Pb-Free Package

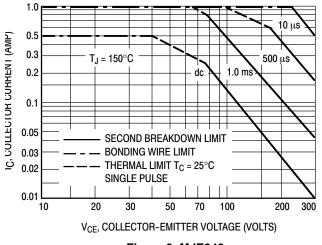
### **ORDERING INFORMATION**

Device	Package	Shipping
MJE340G	TO-225 (Pb-Free)	500 Units/Box

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



**ACTIVE-REGION SAFE OPERATING AREA** 



a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Figure 3 is based on  $T_{J(pk)} = 150^{\circ}$ C;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^{\circ}$ C. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

There are two limitations on the power handling ability of

Figure 3. MJE340

### MJE340G

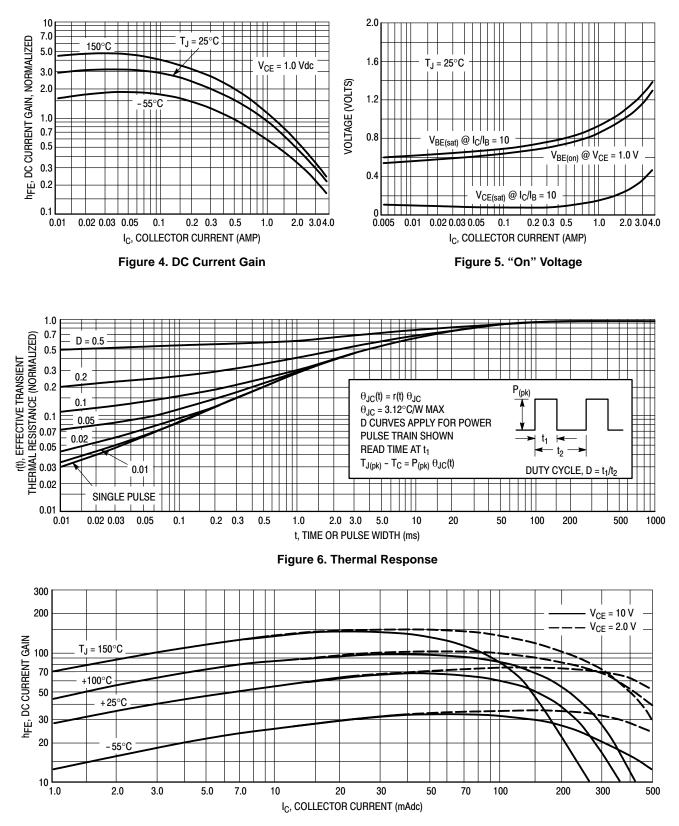
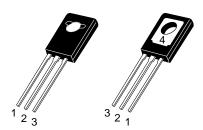


Figure 7. DC Current Gain

### MJE340G

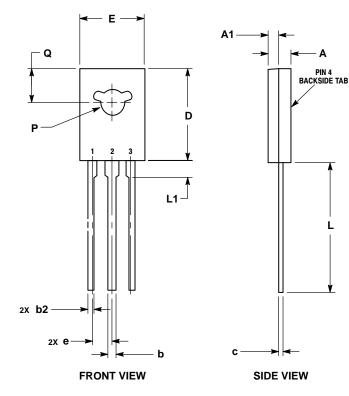
#### PACKAGE DIMENSIONS



TO-225 CASE 77-09 ISSUE AC

FRONT VIEW

BACK VIEW



NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.40	3.00	
A1	1.00	1.50	
b	0.60	0.90	
b2	0.51	0.88	
C	0.39	0.63	
D	10.60	11.10	
Е	7.40	7.80	
е	2.04	2.54	
L	14.50	16.63	
L1	1.27	2.54	
Р	2.90	3.30	
Q	3.80	4.20	
STYLE 1: PIN 1. EMITTER 2., 4. COLLECTOR 3. BASE			

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